



Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, CA 90638
 Phone: (562) 404-4474 * Fax: (562) 404-1773
 ssdi@ssdi-power.com * www.ssdi-power.com

**SDR12U080
 thru
 SDR12U120**

Designer's Data Sheet

Part Number/Ordering Information ^{1/}

SDR12U — — —

- L Screening ^{2/}
 - = Not Screened
 - TX = TX Level
 - TXV = TXV Level
 - S = S Level
- Package
 - G = Cerpack
 - S.5 = SMD.5
- Family/Voltage
 - 080 = 800V
 - 090 = 900V
 - 100 = 1000V
 - 110 = 1100V
 - 120 = 1200V

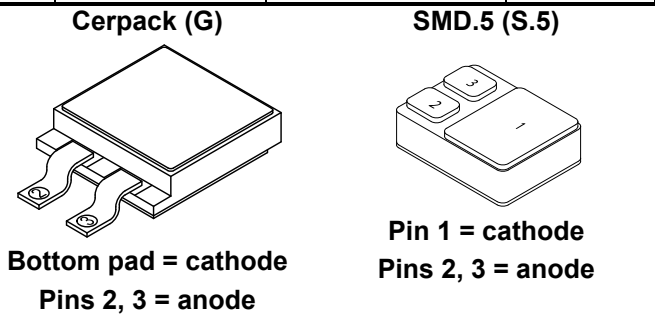
**12 AMP
 ULTRA FAST RECTIFIER
 800 - 1200 VOLTS
 50 nsec**

- FEATURES:**
- Hyper Fast Recovery: typically 30 nS
 - High Surge Rating
 - Low Reverse Leakage Current
 - Low Junction Capacitance
 - Hermetically Sealed Power Package
 - Gold Eutectic Die Attach Available
 - Ultrasonic Aluminum Wire Bonds
 - TX, TXV, or Space Level Screening Available

Maximum Ratings ^{4/}		Symbol	Value	Units
Peak Repetitive Reverse and DC Blocking Voltage ^{3/}	SDR12U080	V_{RRM} V_{RWM} V_R	800	Volts
	SDR12U090		900	
	SDR12U100		1000	
	SDR12U110		1100	
	SDR12U120		1200	
Average Rectified Forward Current (Resistive Load, 60 Hz Sine Wave, T _C = 100°C)		I _O	12	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, T _A = 25°C)		I _{FSM}	120	Amps
Operating & Storage Temperature		T _{OP} & T _{STG}	-65 to +200	°C
Maximum Total Thermal Resistance Junction to Case	Cerpack	R _{θJC}	2.2 (typ 1.7)	°C/W
	SMD.5		1.5 (typ 1.0)	

NOTES:

- ^{1/} For ordering information, price, and availability, contact factory.
- ^{2/} Screening based on MIL-PRF-19500. Screening flows available on request.
- ^{3/} Higher voltages available.
- ^{4/} Both anodes tied together.





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Electrical Characteristic		Symbol	Typ	Max	Units
Instantaneous Forward Voltage Drop ($T_A = 25^\circ\text{C}$, 300 – 500 μsec Pulse)	$I_F = 1\text{ A}$	V_{F1}	1.08	1.20	V_{DC}
	$I_F = 5\text{ A}$	V_{F2}	1.54	1.70	
	$I_F = 10\text{ A}$	V_{F3}	1.85	2.00	
Instantaneous Forward Voltage Drop ($T_A = -55^\circ\text{C}$, 300 – 500 μsec Pulse)	$I_F = 1\text{ A}$	V_{F4}	1.13	-	V_{DC}
	$I_F = 5\text{ A}$	V_{F5}	1.40	-	
	$I_F = 10\text{ A}$	V_{F6}	1.60	-	
Instantaneous Forward Voltage Drop ($T_A = 125^\circ\text{C}$, 300 – 500 μsec Pulse)	$I_F = 1\text{ A}$	V_{F7}	0.83	-	V_{DC}
	$I_F = 5\text{ A}$	V_{F8}	1.37	-	
	$I_F = 10\text{ A}$	V_{F9}	1.80	1.95	
Reverse Leakage Current (100% of rated V_R , 300 μs pulse min.)	$T_A = 25^\circ\text{C}$	I_{R1}	1	10	μA
	$T_A = 100^\circ\text{C}$	I_{R2}	70	-	
	$T_A = 125^\circ\text{C}$	I_{R3}	250	1000	
	$T_A = 150^\circ\text{C}$	I_{R4}	800	-	
Reverse Recovery Time ($I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $I_{RR} = 0.25\text{ A}$, $T_A = 25^\circ\text{C}$)		t_{RR1}	30	50	nsec
Reverse Recovery Time ($I_F = 10\text{ A}$, $di_F/dt = 100\text{ A/us}$)	$T_A = 25^\circ\text{C}$	t_{RR2}	65	-	nsec
		I_{RM2}	5	-	A
Junction Capacitance ($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$)	$V_R = 5\text{ V}_{DC}$	C_J	60	-	pF
	$V_R = 10\text{ V}_{DC}$		47	60	

